

isc Silicon PNP Power Transistor

2SB695

DESCRIPTION

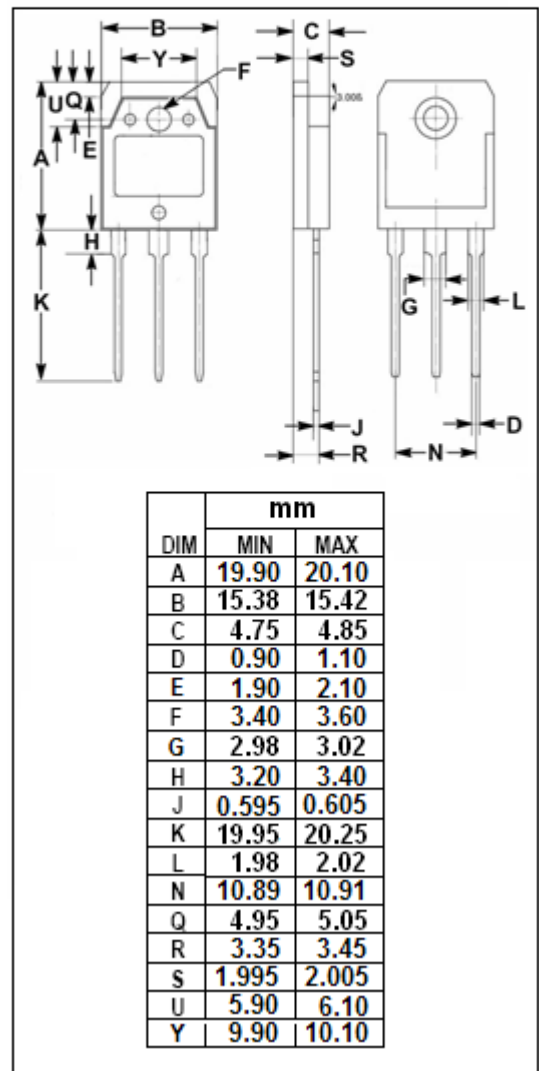
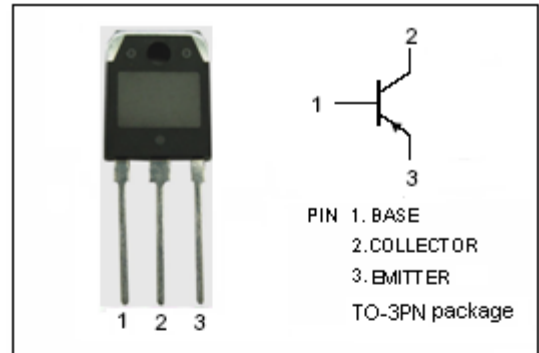
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SD731

APPLICATIONS

- Designed for power amplifier and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | -170 | V |
| V_{CEO} | Collector-Emitter Voltage | -120 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current-Continuous | -7 | A |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 80 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



isc Silicon PNP Power Transistor**2SB695****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---------------|--------------------------------------|---|------|------|------|---------------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C = -30\text{mA}; I_B = 0$ | -120 | | | V |
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C = -1\text{mA}; I_E = 0$ | -170 | | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E = -1\text{mA}; I_C = 0$ | -5 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = -5\text{A}; I_B = -0.5\text{A}$ | | | -1.5 | V |
| $V_{BE(on)}$ | Base -Emitter On Voltage | $I_C = -1\text{A}; V_{CE} = -5\text{V}$ | | | -1.5 | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB} = -170\text{V}; I_E = 0$ | | | -50 | μA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB} = -5\text{V}; I_C = 0$ | | | -50 | μA |
| h_{FE-1} | DC Current Gain | $I_C = -1\text{A}; V_{CE} = -5\text{V}$ | 40 | | 200 | |
| h_{FE-2} | DC Current Gain | $I_C = -5\text{A}; V_{CE} = -5\text{V}$ | 20 | | | |
| C_{OB} | Output Capacitance | $I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1.0\text{MHz}$ | | 350 | | pF |
| f_T | Current-Gain—Bandwidth Product | $I_C = -1\text{A}; V_{CE} = -5\text{V}$ | | 7 | | MHz |